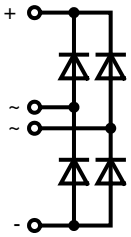
Single Phase Rectifier Bridge

I_{dAV} = 31 A
V_{RRM} = 800-1600 V

Standard and Avalanche Types

V_{RSM} V	V_{BRmin} ① V	V_{RRM} V	Standard Types	Avalanche Types
900		800	VBO 20-08NO2	
1300	1230	1200	VBO 20-12NO2	VBO 20-12AO2
1700	1630	1600	VBO 20-16NO2	VBO 20-16AO2

① For Avalanche Types only



Symbol	Conditions			Maximum Ratings	
I_{dAV} ②	T_C = 85°C, module			31	A
I_{dAVM}	module			40	A
P_{RSM}	$T_{VJ} = T_{VJM}$			3.4	kW
I_{FSM}	T_{VJ} = 45°C;	t = 10 ms	(50 Hz)	300	A
	V_R = 0	t = 8.3 ms	(60 Hz)	315	A
	$T_{VJ} = T_{VJM}$;	t = 10 ms	(50 Hz)	250	A
	V_R = 0	t = 8.3 ms	(60 Hz)	265	A
I^2t	T_{VJ} = 45°C;	t = 10 ms	(50 Hz)	450	A^2s
	V_R = 0	t = 8.3 ms	(60 Hz)	420	A^2s
	$T_{VJ} = T_{VJM}$;	t = 10 ms	(50 Hz)	312	A^2s
	V_R = 0	t = 8.3 ms	(60 Hz)	290	A^2s
T_{VJ}				-40...+150	°C
T_{VJM}				150	°C
T_{stg}				-40...+125	°C
V_{ISOL}	50/60 Hz, RMS	t = 1 min		3000	V~
	$I_{ISOL} \leq$ 1 mA	t = 1 s		3600	V~
M_d	Mounting torque	(M5)		1.5-2	Nm
		(10-32 UNF)		13-18	lb.in.
Weight	Typ.			15	g

Symbol	Conditions		Characteristic Values	
I_R	$V_R = V_{RRM}$	T_{VJ} = 25°C	0.3	mA
		$T_{VJ} = T_{VJM}$	5.0	mA
V_F	I_F = 55 A	T_{VJ} = 25°C	1.8	V
V_{T0}	For power-loss calculations only		0.85	V
r_t			14	mΩ
R_{thJC}	per diode; 120° el.		3.00	K/W
	per module		0.75	K/W
R_{thJH}	per diode; 120° el.		3.40	K/W
	per module		0.85	K/W
d_S	Creeping distance on surface		13	mm
d_A	Creepage distance in air ③		9.5	mm
a	Max. allowable acceleration		50	m/s^2

Data according to IEC 60747 and refer to a single diode unless otherwise stated.
② for resistive load at bridge output
③ with isolated fast-on tabs.

Features

- Avalanche rated parts available
- Package with DCB ceramic base plate
- Isolation voltage 3600 V~
- Planar passivated chips
- Low forward voltage drop
- ¼" fast-on terminals
- UL registered E 72873

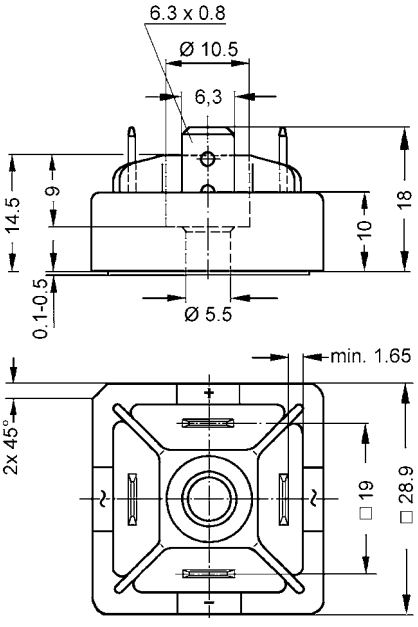
Applications

- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Advantages

- Easy to mount with one screw
- Space and weight savings
- Improved temperature & power cycling

Dimensions in mm (1 mm = 0.0394")



IXYS reserves the right to change limits, test conditions and dimensions.

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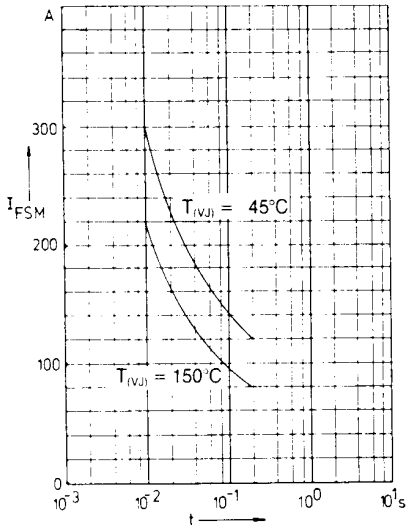

Fig. 1 Surge overload current per diode
I_{FSM}: Crest value, t: duration

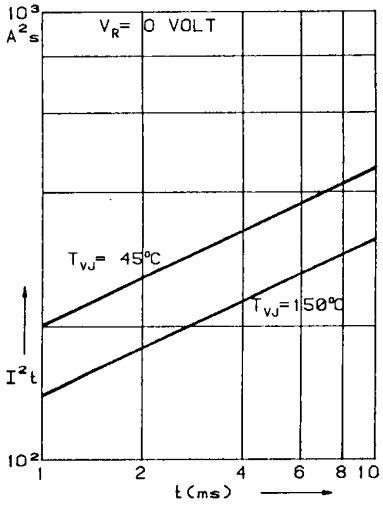

Fig. 2 I^2t versus time (1-10 ms) per diode

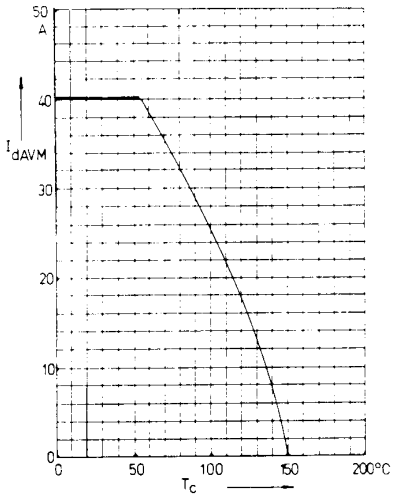

Fig. 3 Max. forward current at case temperature

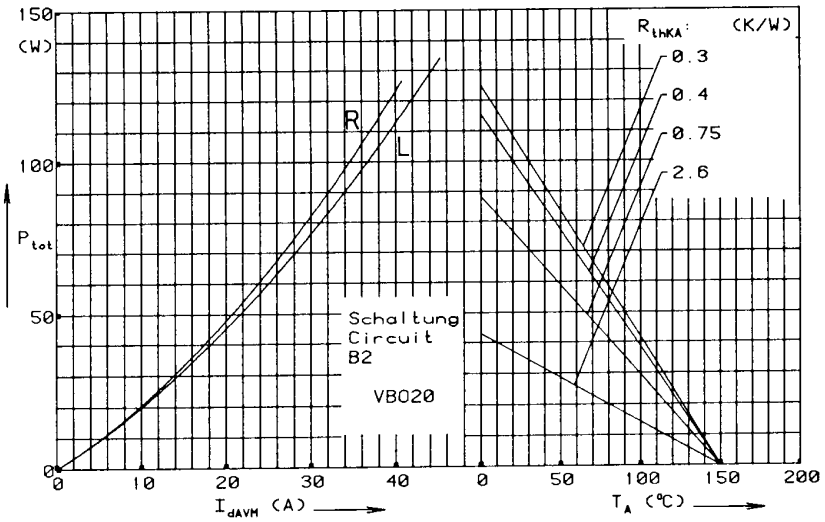

Fig. 4 Power dissipation versus direct output current and ambient temperature

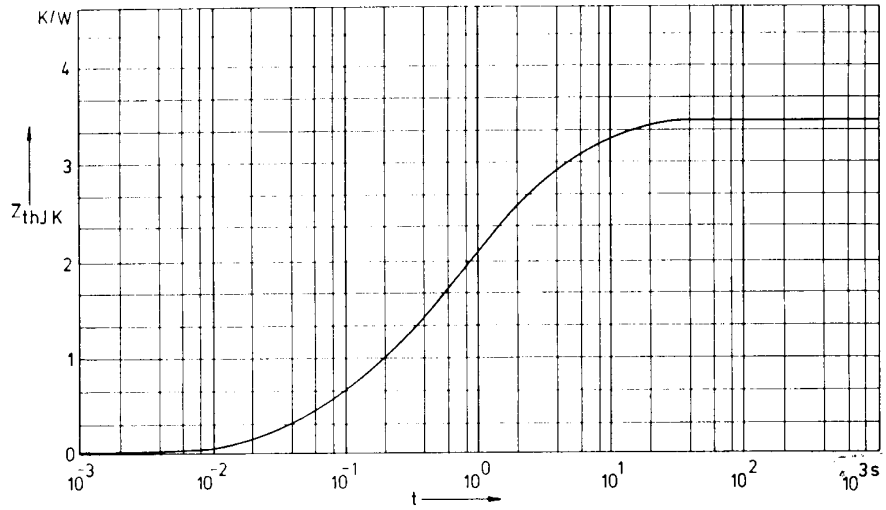

Fig. 5 Transient thermal impedance junction to heatsink per diode

Constants for Z_{thJK} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.775	0.0788
2	1.390	0.504
3	1.255	3.701